

Title (en)

TWO-DIMENSIONAL ELECTRON GAS FIELD-EFFECT TRANSISTOR, ASSOCIATED COMPONENT AND METHODS

Title (de)

ZWEIDIMENSIONALER ELEKTRONENGASFELDEFFEKTTTRANSISTOR, ZUGEHÖRIGE KOMPONENTE UND VERFAHREN

Title (fr)

TRANSISTOR À EFFET DE CHAMP À GAZ D'ÉLECTRONS BIDIMENSIONNEL, COMPOSANT ET PROCÉDÉS ASSOCIÉS

Publication

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Application

EP 18733285 A 20180628

Priority

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- EP 2018067393 W 20180628

Abstract (en)

[origin: WO2019002453A1] The invention concerns a two-dimensional electron gas field-effect transistor (10) comprising: - a drain (14), - a source (16), - a heterojunction (22) comprising: - a first planar layer (26), the first layer (26) being produced from a first material and comprising a first sub-layer (28) formed by acceptor impurities, and - a second planar layer (30), the second layer (30) being produced from a second material and comprising a second sub-layer (32) formed by donor impurities, - a control unit (18) for controlling the current between the drain (14) and the source (16), the control unit (18) being a magnetic field applicator (34) perpendicular to the layers.

IPC 8 full level

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Citation (search report)

See references of WO 2019002453A1

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